

(12) **Patent Application Publication**
LIM et al.

(43) **Pub. Date:** **Jun. 6, 2019**

CPC ***H01L 27/322*** (2013.01); ***H01L 51/5256***
(2013.01); ***H01L 27/3211*** (2013.01); ***H01L***
51/5221 (2013.01); ***H01L 51/5012*** (2013.01);
H01L 51/5206 (2013.01)

(72) Inventors: **Hyeong-Jun LIM**, Paju-si (KR);
Han-Sun PARK, Paju-si (KR);
Hyung-Seok BANG, Paju-si (KR);
Ji-Yeon PARK, Paju-si (KR)

(30) **Foreign Application Priority Data**

Dec. 5, 2017 (KR) 10-2017-0166006

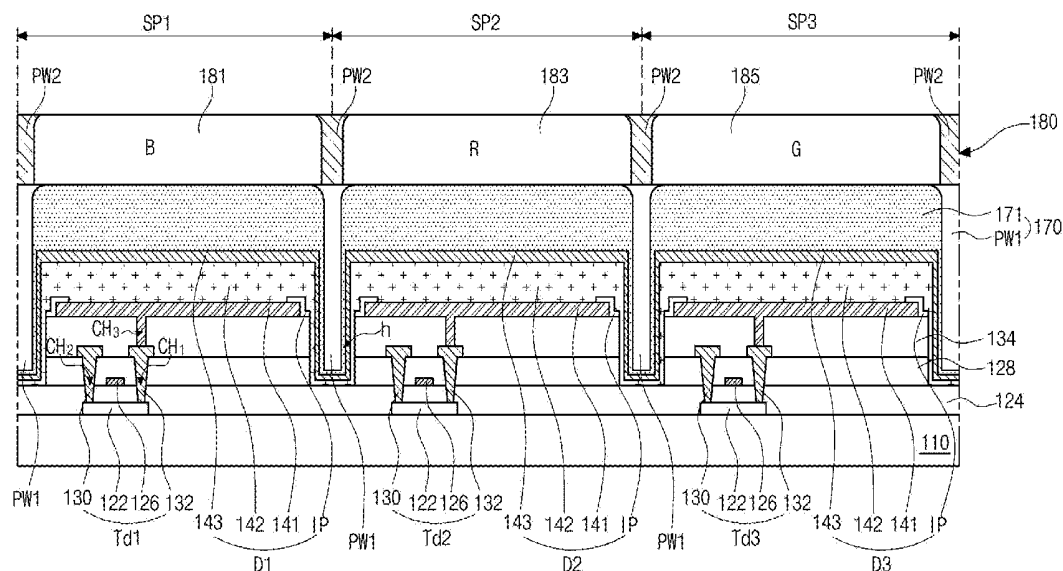
Publication Classification

H01L 27/32	(2006.01)
H01L 51/52	(2006.01)
H01L 51/50	(2006.01)

(57) **ABSTRACT**

An electroluminescent display device is disclosed. The disclosed electroluminescent display device includes a substrate including a plurality of pixel regions; a plurality of light emitting diodes spaced apart from each other on the substrate and each corresponding to the plurality of pixel regions, respectively; a plurality of encapsulation films respectively covering each of the light emitting diodes of the plurality of light emitting diodes, wherein the plurality of encapsulation films has a first refractive index; a first partition wall disposed between each of the encapsulation films of the plurality of encapsulation films, wherein the first partition wall corresponds to a boundary between the plurality of pixel regions and has a second refractive index lower than the first refractive index; and a color filter layer disposed on the plurality of encapsulation films and the first partition wall.

100



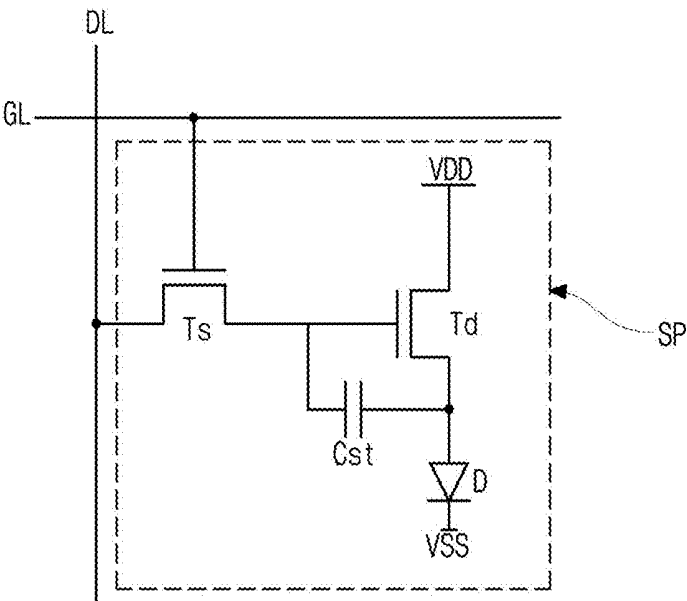


FIG. 1

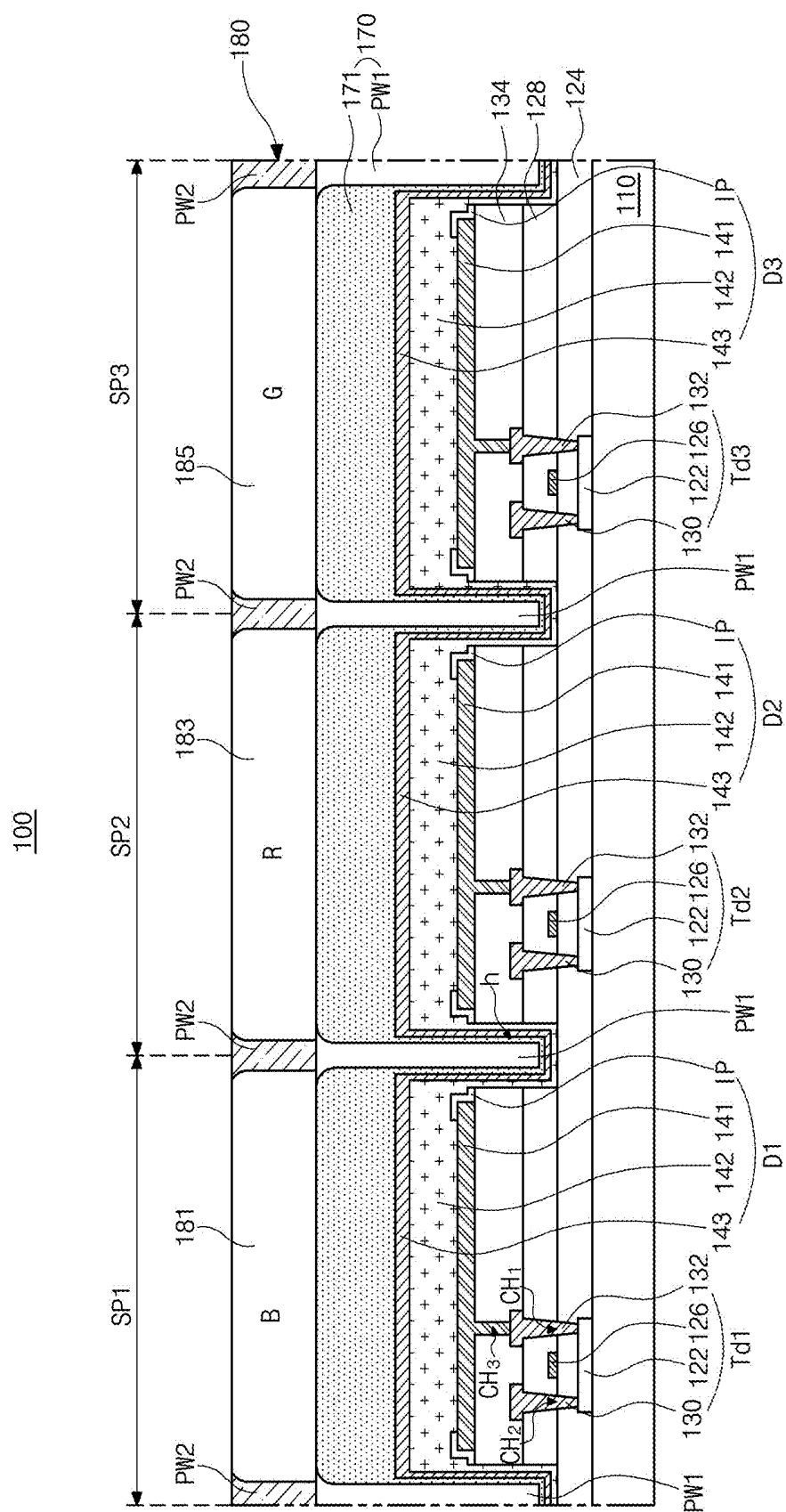


FIG. 2

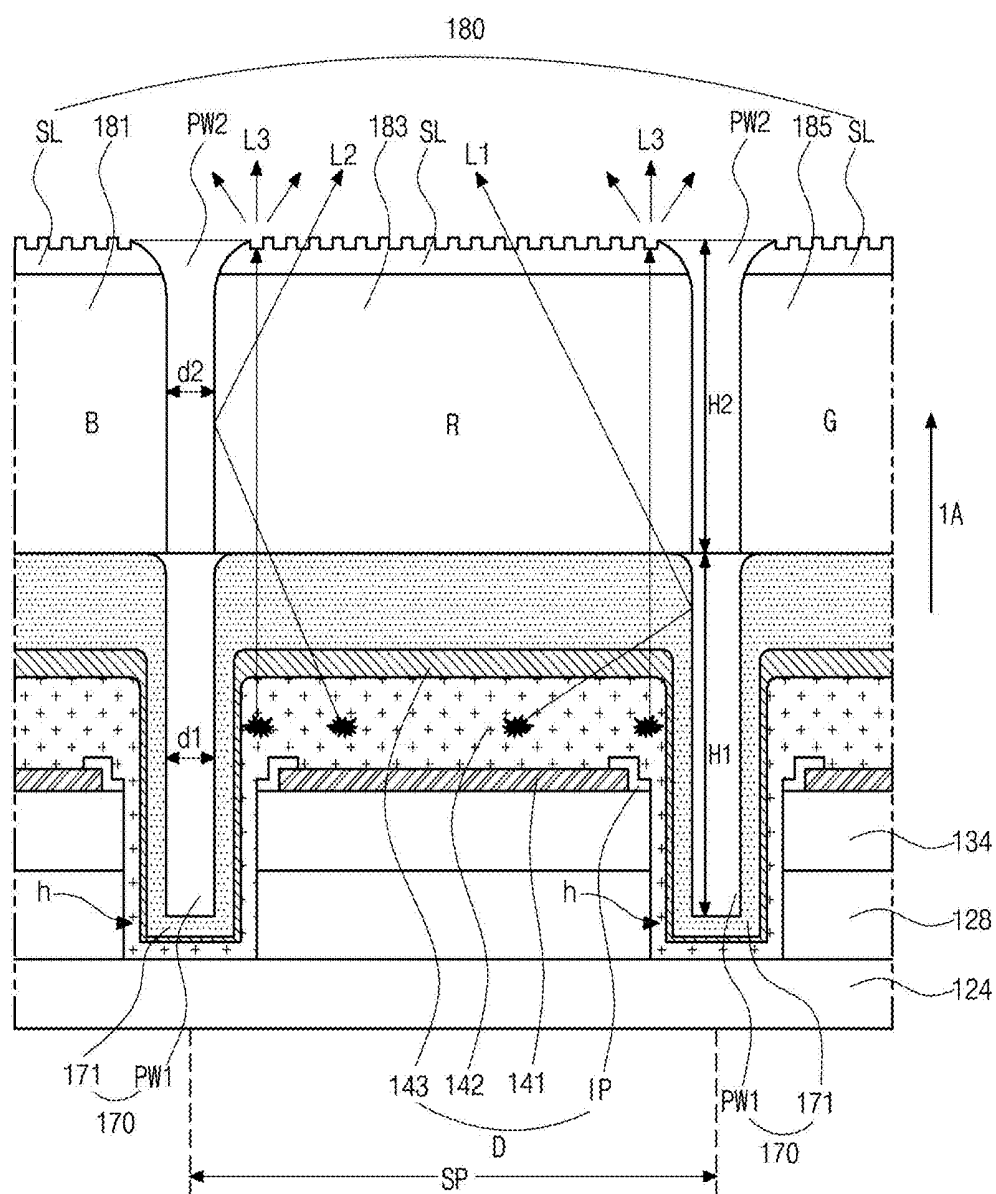


FIG. 3

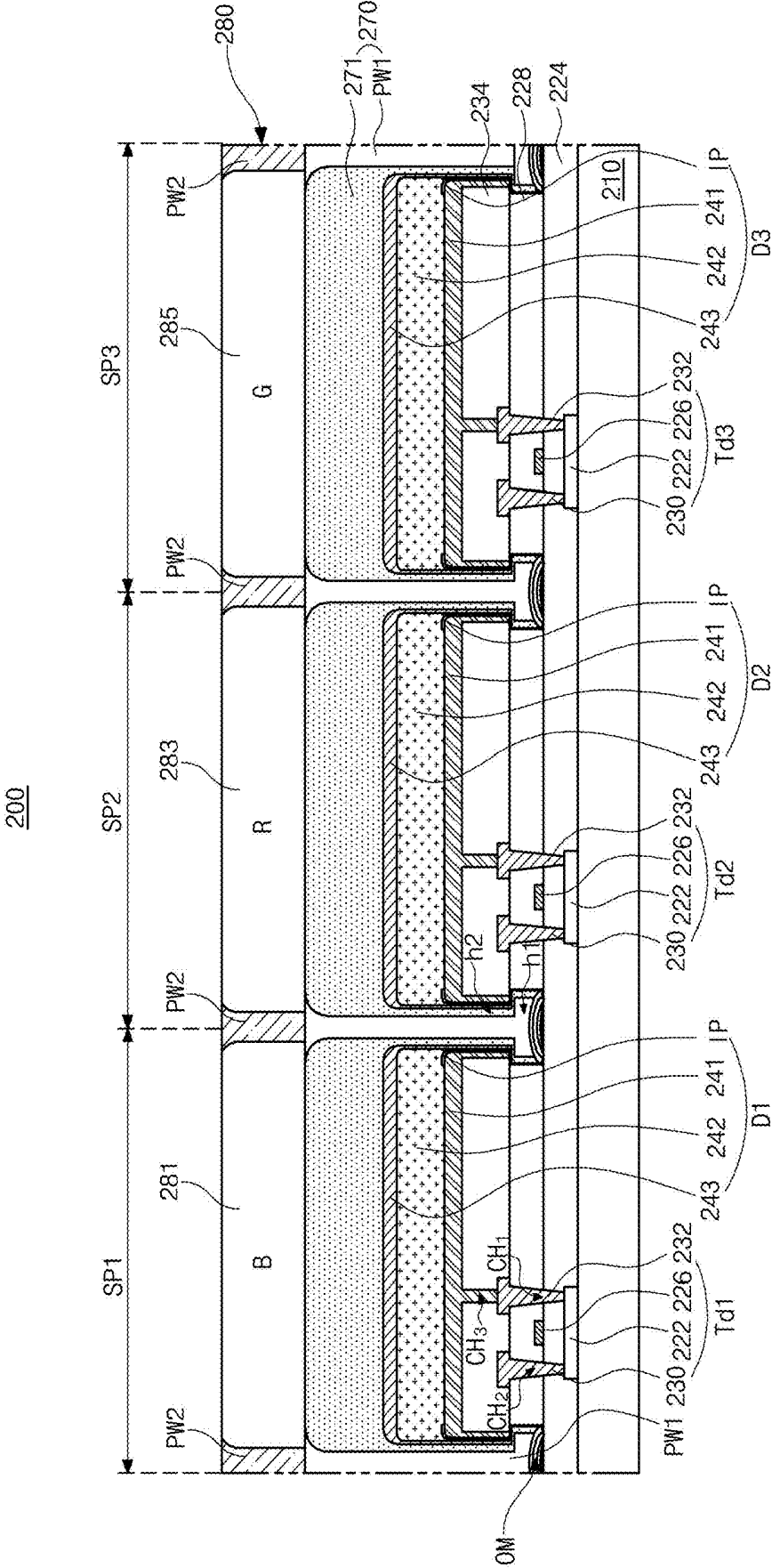


FIG. 4

FIG. 5

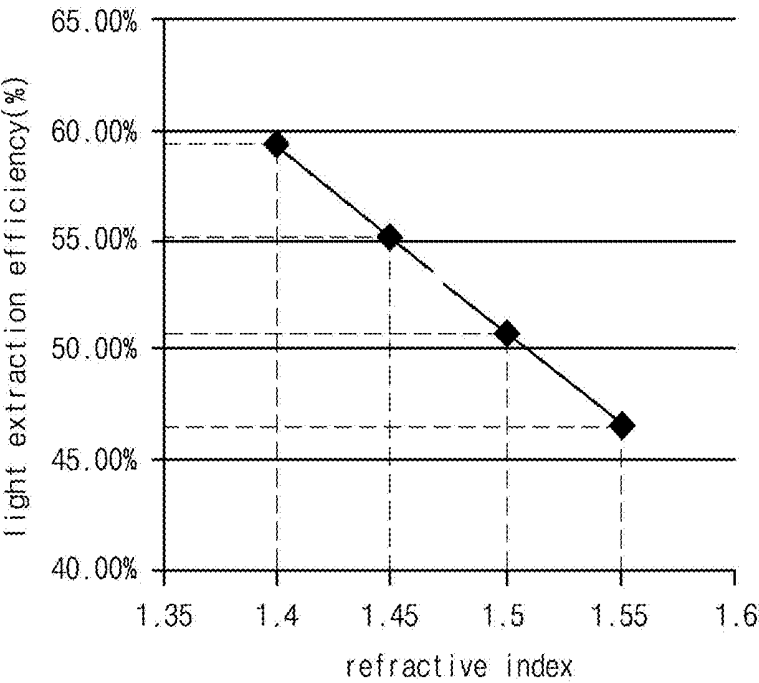


FIG. 6

ELECTROLUMINESCENT DISPLAY DEVICE

[0001] This application claims priority from and the benefit of Korean Patent Application No. 10-2017-0166006, filed on Dec. 5, 2017, which is incorporated herein by reference in its entirety for all purposes as if fully set forth herein.

BACKGROUND

Technical Field

[0002] The present disclosure relates to an electroluminescent display device, and more particularly, to an electroluminescent display device in which a partition wall having a low refractive index is disposed so that light extraction efficiency may be improved and color mixture may be substantially prevented.

Discussion of the Related Art

[0003] In recent years, flat panel displays having excellent characteristics, such as being thin, lightweight, and having low power consumption have been widely developed and applied to various fields. Among the flat panel displays, an electroluminescent display device is a device in which electrical charge carriers are injected into a light-emitting layer formed between a cathode and an anode. The cathode is an electron-injecting electrode. The anode is a hole-injecting electrode. Excitons are then formed and finally, radiative recombination of the excitons occurs, thereby emitting light.

[0004] The electroluminescent display device is formed using a flexible substrate, such as plastic because it is self-luminous and has excellent contrast ratios. The electroluminescent display device has a response time of several microseconds, which is advantageous for displaying moving images. The electroluminescent display device also has wide viewing angles and is stable under low temperatures. Because the electroluminescent display device is driven by a low voltage of direct current (DC) of about 5 V to 15 V, it is easy to design and manufacture driving circuits. Recently, as the size of substrates has been increased and display devices have evolved to have a high resolution, pixel pitch has been decreased and color mixture has become a problem.

SUMMARY

[0005] Accordingly, example embodiments of the present disclosure are directed to an electroluminescent display device that substantially obviates one or more of the problems due to limitations and disadvantages of the related art. An aspect of the present disclosure is to provide an electroluminescent display device with high resolution in which a first partition wall and a second partition wall having a relatively low refractive index are disposed so that light extraction efficiency may be improved and/or color mixture may be prevented.

[0006] To achieve these and other aspects of the inventive concepts, and in accordance with the purpose of the present invention, as embodied and broadly described, an electroluminescent display device includes: a substrate including a plurality of pixel regions; a plurality of light emitting diodes spaced apart from each other on the substrate and each corresponding to the plurality of pixel regions, respectively; a plurality of encapsulation films respectively covering each

of the light emitting diodes of the plurality of light emitting diodes, wherein the plurality of encapsulation films has a first refractive index; a first partition wall disposed between each of the encapsulation films of the plurality of encapsulation films, wherein the first partition wall corresponds to a boundary between the plurality of pixel regions and has a second refractive index lower than the first refractive index; and a color filter layer disposed on the plurality of encapsulation films and the first partition wall, wherein the color filter layer includes a plurality of color filter patterns having a third refractive index and the color filter layer further includes a second partition wall disposed between each of the plurality of color filter patterns, and wherein the second partition wall has a fourth refractive index lower than the third refractive index.

[0007] It is to be understood that both the foregoing general description and the following detailed description are by example and explanatory, and are intended to provide further explanation of the inventive concepts as claimed.

BRIEF DESCRIPTION OF THE DRAWINGS

[0008] The accompanying drawings, which are included to provide a further understanding of the present disclosure, and which are incorporated in and constitute a part of this specification, illustrate example embodiments of the present disclosure and together with the description serve to explain various principles of the present disclosure. In the drawings: [0009] FIG. 1 is a circuit diagram illustrating a single pixel region of an electroluminescent display device according to an example embodiment of the present disclosure.

[0010] FIG. 2 is a cross-sectional view illustrating an electroluminescent display device according to a first example embodiment of the present disclosure.

[0011] FIG. 3 is an enlarged view of a portion of an electroluminescent display device according to the first example embodiment of the present disclosure.

[0012] FIG. 4 is a cross-sectional view illustrating an electroluminescent display device according to a second example embodiment of the present disclosure.

[0013] FIG. 5 is an enlarged view of a portion of the electroluminescent display device according to the second example embodiment of the present disclosure.

[0014] FIG. 6 is a graph illustrating light extraction efficiency according to refractive indices of first and second partition walls according to the first and second example embodiments of the present disclosure.

DETAILED DESCRIPTION

[0015] Reference will now be made in detail to example embodiments of the present disclosure, examples of which may be illustrated in the accompanying drawings.

First Example Embodiment

[0016] FIG. 1 is a circuit diagram illustrating a single pixel region of an electroluminescent display device according to an example embodiment of the present disclosure.

[0017] As illustrated in FIG. 1, the electroluminescent display device according to an example embodiment of the present disclosure may include a gate line GL, a data line DL, a switching thin film transistor Ts, a driving thin film transistor Td, a storage capacitor Cst and a light-emitting diode D. The gate line GL and the data line DL may cross each other to define a pixel region SP. The switching thin

film transistor Ts, the driving thin film transistor Td, the storage capacitor Cst and the light-emitting diode D may be formed in the pixel region SP.

[0018] A gate electrode of the switching thin film transistor Ts may be connected to the gate line GL and a source electrode of the switching thin film transistor Ts may be connected to the data line DL. A gate electrode of the driving thin film transistor Td may be connected to a drain electrode of the switching thin film transistor Ts and a source electrode of the driving thin film transistor Td may be connected to a high voltage supply VDD. An anode of the light-emitting diode D may be connected to a drain electrode of the driving thin film transistor Td and a cathode of the light-emitting diode D may be connected to a low voltage supply VSS. The storage capacitor Cst may be connected to the gate electrode and the drain electrode of the driving thin film transistor Td.

[0019] The electroluminescent display device may be driven to display an image. For example, when the switching thin film transistor Ts is turned on by a gate signal applied through the gate line GL, a data signal from the data line DL may be applied both to the gate electrode of the driving thin film transistor Td and/or to an electrode of the storage capacitor Cst through the switching thin film transistor Ts.

[0020] When the driving thin film transistor Td is turned on by the data signal, an electric current flowing through the light-emitting diode D may be controlled, thereby displaying an image. The light-emitting diode D may emit light due to the current supplied through the driving thin film transistor Td from the high voltage supply VDD. For example, the amount of current flowing through the light-emitting diode D may be proportional to the magnitude of the data signal. Additionally, the intensity of light emitted by the light-emitting diode D may be proportional to the amount of current flowing through the light-emitting diode D. Thus, pixel regions SP may show different gray levels depending on the magnitude of the data signal, and as a result, the electroluminescent display device displays an image.

[0021] The storage capacitor Cst may maintain charges corresponding to the data signal for a frame when the switching thin film transistor Ts is turned off. Accordingly, even if the switching thin film transistor Ts is turned off, the storage capacitor Cst allows the amount of current flowing through the light-emitting diode D to be constant and/or the gray level shown by the light-emitting diode D to be maintained until a next frame. Finally, a transistor and/or a capacitor other than the switching and driving thin film transistors Ts and Td and/or the storage capacitor Cst may be further added in the pixel region SP.

[0022] FIG. 2 is a cross-sectional view illustrating an electroluminescent display device according to the first example embodiment of the present disclosure.

[0023] As illustrated in FIG. 2, an electroluminescent display device 100 may include a substrate 110, thin film transistors Td1, Td2, and Td3 and light emitting diodes D1, D2, and D3. Thin film transistors Td1, Td2, and Td3 and light emitting diodes D1, D2, and D3 may be respectively formed in pixel regions SP1, SP2, and SP3 disposed on the substrate 110. An encapsulation layer 170 may be disposed on the light emitting diodes D1, D2, and D3. A color filter layer 180 disposed on the encapsulation layer 170.

[0024] The substrate 110 may also be referred to as a lower substrate, a thin film transistor (TFT) substrate, or a back-plane, in which case each of the pixel regions SP1, SP2, and SP3 may refer to a unit in which a specific type of color filter

pattern among color filter patterns 181, 183, and 185 may be formed. Thus, a specific color may be emitted. For example, the pixel regions SP1, SP2, and SP3 may include a blue pixel region SP1, a red pixel region SP2, and a green pixel region SP3. However, the pixel regions SP1, SP2, and SP3 are not limited thereto, and may further include a white pixel region.

[0025] A semiconductor layer 122 may be formed in each of the pixel regions SP1, SP2, and SP3. A gate insulating layer 124 may be formed on the semiconductor layer 122 over substantially all of the substrate 110 including the pixel regions SP1, SP2, and SP3. The semiconductor layer 122 may include an active area that may be formed of one or more intrinsic semiconductor materials and disposed at the center of the semiconductor layer 122. The semiconductor layer may further include a source area and/or a drain area that are formed of one or more impurity-doped semiconductor materials and are respectively formed at left and right positions of the active area.

[0026] A gate electrode 126 may be formed on the gate insulating layer 124 corresponding to the semiconductor layer 122 and an interlayer insulating layer 128 may be formed on the gate electrode 126. The interlayer insulating layer 128 and the gate insulating layer 124 may include first and second contact holes CH1 and CH2 configured to respectively expose the source area and the drain area of the semiconductor layer 122.

[0027] A source electrode 132 and a drain electrode 130 spaced apart from each other are formed on the interlayer insulating layer 128 corresponding to the semiconductor layer 122. The source electrode 132 and the drain electrode 130 may be respectively connected to the source area and the drain area of the semiconductor layer 122 through the first and second contact holes CH1 and CH2. The semiconductor layer 122, the gate electrode 126, the source electrode 132, and the drain electrode 130 formed in each of the pixel regions SP1, SP2, and SP3 may respectively constitute each of the thin film transistors Td1, Td2, and Td3.

[0028] Although coplanar type thin film transistors Td1, Td2, and Td3 are illustrated in FIG. 2 as an example, example embodiments are not limited thereto, and staggered type thin film transistors may also be formed. Although only the driving thin film transistors Td1, Td2, and Td3 are illustrated in FIG. 2, a plurality of thin film transistors, such as the switching thin film transistor Ts of FIG. 1 having the same or substantially the same structure as the driving thin film transistors Td1, Td2, and Td3 may be formed in a single pixel region.

[0029] Although not illustrated in FIG. 2, a gate line GL, a data line DL, and/or a power line may cross each other to define the pixel regions SP1, SP2, and SP3 in FIG. 2. The switching thin film transistor Ts of FIG. 2 may be connected to the gate line GL and the data line DL. Each driving thin film transistor Td1, Td2, and Td3 may be connected to the switching thin film transistor Ts of FIG. 2 and/or the power line.

[0030] A passivation layer 134 may be formed on each of the thin film transistors Td1, Td2, and Td3. The passivation layer 134 may include a third contact hole CH3 configured to expose the source electrode 132. An overcoat layer may be disposed on the passivation layer 134. In this case, the passivation layer 134 and the overcoat layer may include the third contact hole CH3 exposing the source electrode 132.

[0031] Holes h configured to partition the pixel regions SP1, SP2, and SP3 may be formed in the passivation layer

134 and the interlayer insulating layer **128**. The light emitting diodes **D1**, **D2**, and **D3** may be partitioned by the holes **h** in the passivation layer **134** and the interlayer insulating layer **128** so that the light emitting diodes **D1**, **D2**, and **D3** may respectively correspond to the pixel regions **SP1**, **SP2**, and **SP3**. The light emitting diodes **D1**, **D2**, and **D3** may be spaced apart from each other and respectively disposed in the pixel regions **SP1**, **SP3**, and **SP3**.

[0032] Although the holes **h** are illustrated as being formed in the passivation layer **134** and the interlayer insulating layer **128** in FIG. 2, this is merely an example. The electroluminescent display device **100** may have various other structures in which holes **h** capable of partitioning the light emitting diodes **D1**, **D2**, and **D3** corresponding to the pixel regions **SP1**, **SP2**, and **SP3** are formed. Holes **h** may be formed by performing a light-exposing process using a photo mask and a development process.

[0033] A first electrode **141** may be disposed on the passivation layer **134**. The first electrode **141** may be an anode or cathode for supplying one of holes or electrons to a light-emitting layer **142**. Where the first electrode **141** of the electroluminescent display device is an anode, the first electrode **141** may be formed as a single layer of one or more transparent conductive materials, such as indium tin oxide (ITO). Alternatively, the first electrode **141** may be formed of one or more conductive materials with relatively high reflectance, such as a laminated structure of aluminum and titanium (Ti/Al/Ti), a laminated structure of Al and ITO (ITO/Al/ITO), an APC alloy, and/or a laminated structure of the APC alloy and ITO (ITO/APC/ITO) to obtain a micro cavity effect. The APC alloy refers to an alloy of silver (Ag), palladium (Pd), and copper (Cu).

[0034] The first electrode **141** may be connected to the source electrode **132** of each of the thin film transistors **Td1**, **Td2**, and **Td3** through the third contact hole **CH3** formed in the passivation layer **134** and may be separately formed in each of the pixel regions **SP1**, **SP2**, and **SP3**. Although the electroluminescent display device **100** has been described by assuming that the thin film transistors **Td1**, **Td2**, and **Td3** are N-type thin film transistors and the first electrode **141** may be connected to the source electrode **132**, example embodiments are not limited thereto. When the thin film transistors **Td1**, **Td2**, and **Td3** are P-type thin film transistors, the first electrode **141** may be connected to the drain electrode **130**.

[0035] An insulating pattern **IP** may be configured to cover an edge of the first electrode **141** may be disposed on the first electrode **141**. The insulating pattern **IP** may be disposed to cover a side surface and a portion of an upper surface of the first electrode **141**. The insulating pattern **IP** may be formed of silicon oxide, but example embodiments are not limited thereto. The insulating pattern **IP** may mitigate a step difference of the first electrode **141** and improve current efficiency. For example, when forming the light-emitting layer **142** on the first electrode **141**, the light-emitting layer **142** may be formed to have a relatively small thickness on a stepped area of the first electrode **141** so that a current that does not contribute to emission may be substantially prevented from being focused.

[0036] The light-emitting layer **142** may be disposed on the first electrode **141** and the insulating pattern **IP** and the light-emitting layer **142** may emit white light. For example, the light-emitting layer **142** may have a tandem white structure in which a plurality of light-emitting layers is stacked to emit white light. The light-emitting layer **142** may

include a first light-emitting layer configured to emit blue light and a second light-emitting layer disposed on the first light-emitting layer and configured to emit light having a color that turns white when mixed with blue. The second light-emitting layer may be a light-emitting layer configured to emit yellow-green light, but example embodiments are not limited thereto. A light-emitting layer **142** configured to emit one of blue light, red light, and green light may be disposed in each of the pixel regions **SP1**, **SP2**, and **SP3**.

[0037] A luminescent material of the light-emitting layer **142** may be one or more organic luminescent materials having a refractive index of about 1.8 or higher or one or more inorganic luminescent materials, such as a quantum dot. The light-emitting layer **142** may be disposed in a shape that follows the approximate morphologies of the entire or substantially entire surfaces of the pixel regions **SP1**, **SP2**, and **SP3**. The light-emitting layer **142** may be disposed in a shape that follows the approximate morphology of the first electrode **141**, the insulating pattern **IP** formed in each of the pixel regions **SP1**, **SP2**, and **SP3**, the holes **h** formed in the passivation layer **134**, and the interlayer insulating layer **128**.

[0038] A second electrode **143** for supplying one of electrons or holes to the light-emitting layer **142** may be disposed on the light-emitting layer **142**. The second electrode **143** may be a cathode or an anode. Where the second electrode **143** of the electroluminescent display device **100** is a cathode, the second electrode **143** may be formed along the morphology of the light-emitting layer **142**. In this example, the second electrode **143** may be formed to cover the light-emitting layer **142** along the shape of the light-emitting layer **142**.

[0039] The second electrode **143** may be formed of one or more transparent conductive materials, such as ITO and/or indium zinc oxide (IZO) capable of transmitting light or may be formed of one or more semi-transmissive conductive materials, such as magnesium (Mg), silver (Ag), or an alloy of Mg and Ag. Accordingly, the first electrode **141**, the insulating pattern **IP**, the light-emitting layer **142**, and the second electrode **143** may overlap with each other and form each of the light emitting diodes **D1**, **D2**, and **D3**. The light emitting diodes **D1**, **D2**, and **D3** may be spaced apart from each other and be disposed corresponding to the pixel regions **SP1**, **SP2**, and **SP3**, respectively.

[0040] The encapsulation layer **170** may be disposed on the light emitting diodes **D1**, **D2**, and **D3** formed corresponding to the pixel regions **SP1**, **SP2**, and **SP3**, respectively. The encapsulation layer **170** of the electroluminescent display device **100** may include an encapsulation film **171** having a first refractive index and a first partition wall **PW1** having a second refractive index lower than the first refractive index.

[0041] The encapsulation film **171** may be formed along the morphology of the light emitting diodes **D1**, **D2**, and **D3** corresponding to the pixel regions **SP1**, **SP2**, and **SP3**, respectively. The encapsulation film **171** may be formed along the morphology of the second electrode **143** disposed at the uppermost portions of the light emitting diodes **D1**, **D2**, and **D3**. Because the encapsulation film **171** may be disposed along the morphology of the second electrode **143**, a groove may be formed in the encapsulation film **171** corresponding to a boundary between the pixel regions **SP1**, **SP2**, and **SP3**. The encapsulation film **171** may be formed of an inorganic film and/or may have a multilayer structure. For

example, the encapsulation film **171** may include at least one layer formed of silicon nitride, aluminum nitride, zirconium nitride, titanium nitride, hafnium nitride, tantalum nitride, silicon oxide, aluminum oxide, and/or titanium oxide.

[0042] The first partition wall **PW1**, which may be bar-shaped, may be disposed in the groove of the encapsulation film **171** corresponding to the boundary between the pixel regions **SP1**, **SP2**, and **SP3**. Although a width of an upper portion of the first partition wall **PW1** is illustrated in FIGS. **2-5** as progressively increasing, this is merely an example, and the first partition wall **PW1** may have the same or substantially the same width throughout. The first partition wall **PW1** may be made of one or more organic materials having a second refractive index lower than a first refractive index of the encapsulation film **171**. For example, the first refractive index may be in a range of about 1.56 to 1.85 and the second refractive index may be in a range of about 1.0 to 1.55, but example embodiments are not limited thereto.

[0043] Because the first partition wall **PW1** may have a refractive index lower than that of the encapsulation film **171**, light that may be incident obliquely on the encapsulation film **171** from the light-emitting layer **142** of the light emitting diodes **D1**, **D2**, and **D3** may be reflected by the first partition wall **PW1** and output to upper areas of the corresponding pixel regions **SP1**, **SP2**, and **SP3**. Accordingly, light extraction efficiency of the electroluminescent display device **100** may be improved and color mixture may be substantially prevented. In addition, permeation of oxygen and/or moisture into the light-emitting layer **142** and the second electrode **143** may be more substantially prevented by the encapsulation films **171** and the first partition walls **PW1** disposed between the encapsulation films **171** configured to cover the light emitting diodes **D1**, **D2**, and **D3**.

[0044] The color filter layer **180** may be disposed on the encapsulation layer **170**. The color filter layer **180** may include the color filter patterns **181**, **183**, and **185** formed corresponding to the pixel regions **SP1**, **SP2**, and **SP3**, respectively. The color filter **180** may further include a bar-shaped second partition wall **PW2** disposed between the color filter patterns **181**, **183**, and **185**. Although a width of an upper portion of the second partition wall **PW2** is illustrated in FIGS. **2-5** as progressively increasing, this is merely an example, and the second partition wall **PW2** may have the same or substantially the same width throughout.

[0045] The color filter patterns **181**, **183**, and **185** may have a third refractive index and the second partition wall **PW2** may have a fourth refractive index lower than the third refractive index. For example, the third refractive index may be in a range of about 1.6 to 1.85 and the fourth refractive index may be in a range of about 1.0 to 1.55, but example embodiments are not limited thereto.

[0046] The second partition wall **PW2** may be formed of silicon oxide, but example embodiments are not limited thereto. Because the second partition wall **PW2** may have a refractive index lower than that of the color filter patterns **181**, **183**, and **185**, light that may be incident obliquely on the color filter patterns **181**, **183**, and **185** from the light-emitting layer **142** of the light emitting diodes **D1**, **D2**, and **D3** may be reflected by the second partition wall **PW2** and be output to upper areas of the corresponding pixel regions **SP1**, **SP2**, and **SP3**. Accordingly, color mixture in a viewing angle direction may be substantially prevented.

[0047] Because the second partition wall **PW2** between the color filter patterns **181**, **183**, and **185** has a relatively

fine width, an emissive area may be increased in comparison to a related art case in which a black matrix may be disposed. The second partition wall **PW2** of the electroluminescent display device may be formed corresponding to the first partition wall **PW1**. For example, the first partition wall **PW1** and the second partition wall **PW2** may be parallel or substantially parallel to each other in a first direction perpendicular to the substrate **110**.

[0048] Because the first partition wall **PW1** and the second partition wall **PW2** may be parallel or substantially parallel to each other in the first direction, light that may be output from the light emitting diodes **D1**, **D2**, and **D3** respectively formed in the pixel regions **SP1**, **SP2**, and **SP3** may be output to upper areas of the corresponding pixel regions **SP1**, **SP2**, and **SP3**. Accordingly, light extraction efficiency may be improved and color mixture may be substantially prevented.

[0049] FIG. **3** is an enlarged view of a portion of an electroluminescent display device according to the first example embodiment of the present disclosure.

[0050] Although not illustrated in FIG. **3**, the electroluminescent display device **100** of FIG. **2** may include a substrate **110** of FIG. **2**. Light emitting diodes **D** may be disposed on the substrate **110** of FIG. **2**, an encapsulation layer **170** may be disposed on the light emitting diodes **D**, and a color filter layer **180** may be disposed on the encapsulation layer **170**. An interlayer insulating layer **128** and a passivation layer **134** may be disposed between the substrate **110** and the light emitting diodes **D**. Because the holes **h** configured to partition pixel regions **SP** are formed in the passivation layer **134** and the interlayer insulating layer **128**, the light emitting diodes **D** may be formed corresponding to the pixel regions **SP**. Furthermore, because the holes **h** are formed in the passivation layer **134** and the interlayer insulating layer **128**, a bank layer, which may be formed in a related art electroluminescent display device to partition pixel regions **SP**, may be omitted. Therefore, a process of forming the electroluminescent display device according to example embodiments of the present disclosure may be simplified.

[0051] A first electrode **141** may be disposed on the passivation layer **134** and an insulating pattern **IP** configured to cover an edge of the first electrode **141** may be disposed on the first electrode **141**. When forming a light-emitting layer **142** on the first electrode **141** using the insulating pattern **IP**, the light-emitting layer **142** may be formed to have a relatively small thickness on a stepped area of the first electrode **141**. Therefore, a current that does not contribute to emission may be substantially prevented from being focused, and current efficiency may be improved. The light-emitting layer **142** may be disposed on the first electrode **141** and the insulating pattern **IP**. The light-emitting layer **142** may be disposed in a shape that follows the morphology of the first electrode **141**, the insulating pattern **IP**, and the holes **h** formed in the passivation layer **134** and the interlayer insulating layer **128**. A second electrode **143** may be disposed on the light-emitting layer **142**. The second electrode **143** may be disposed in a shape that follows the morphology of the light-emitting layer **142**. Accordingly, the first electrode **141**, the insulating pattern **IP**, the light-emitting layer **142**, and the second electrode **143** may form the light emitting diodes **D**. Adjacent light emitting diodes **D** may be spaced apart from each other and may be disposed corresponding to the pixel regions **SP**.

[0052] The encapsulation layer 170, which may include an encapsulation film 171 having a first refractive index and a first partition wall PW1 having a second refractive index lower than the first refractive index, may be disposed on the light emitting diodes D. The encapsulation film 171 may be formed along the morphology of the light emitting diodes D. The encapsulation film 171 may be formed along the morphology of the second electrode 143 disposed at the uppermost portions of the light emitting diodes D.

[0053] Because the encapsulation film 171 may be disposed along the morphology of the second electrode 143, the electroluminescent display device 100 may have a structure in which the encapsulation film 171 covers each of the light emitting diodes D. Therefore, permeation of oxygen and/or moisture into the light-emitting layer 142 and the second electrode 143 may be substantially prevented. The encapsulation film 171 may be formed of an inorganic film and/or may have a multilayer structure.

[0054] The first partition wall PW1 may be disposed in the groove of the encapsulation film 171 corresponding to the boundary between the pixel regions SP. A middle portion of the first partition wall PW1 may have a bar shape and an upper portion of the first partition wall PW1 may have a shape in which a width progressively increases upward. However, this is merely an example and the first partition wall PW1 may be formed such that the upper portion and the middle portion have the same or substantially the same width. For example, a width d1 of the middle portion of the first partition wall PW1 may be in a range of about 2 micrometers (μm) to 3 μm . The width of the upper portion of the first partition wall PW1 may be larger than or equal to the width d1 of the middle portion of the first partition wall PW1. However, example embodiments are not limited thereto and the widths of the upper portion and the middle portion of the first partition wall PW1 may be modified in various ways according to, for example, the size and/or resolution of the pixel regions SP.

[0055] A height H1 of the first partition wall PW1 may be in a range of about 7 μm to 9 μm , but example embodiments are not limited thereto. The height H1 may be modified in various ways according to, for example, a thickness of the passivation layer 134, the interlayer insulating layer 128, and/or the light emitting diodes D.

[0056] The passivation layer 134 and the interlayer insulating layer 128 may be separated corresponding to the pixel regions SP by the first partition wall PW1. In this example, the first partition wall PW1 may be made of one or more organic materials having a second refractive index lower than the first refractive index of the encapsulation film 171. For example, the first refractive index may be in a range of about 1.6 to 1.85 and the second refractive index may be in a range of about 1.0 to 1.55, but example embodiments are not limited thereto.

[0057] Because the first partition wall PW1 may have a refractive index lower than that of the encapsulation film 171, light that may be incident obliquely on the encapsulation film 171 from the light-emitting layer 142 of the light emitting diodes D may be reflected by the first partition wall PW1 and may be output to upper areas of the corresponding pixel regions SP. Accordingly, light extraction efficiency of the electroluminescent display device 100 may be improved and color mixture may be substantially prevented. Because the first partition wall PW1 may be formed between the encapsulation films 171 configured to cover the light emit-

ting diodes D, permeation of oxygen and/or moisture into the light-emitting layer 142 and the second electrode 143 may be substantially prevented. Therefore, efficiency may be improved.

[0058] The color filter layer 180 may be disposed on the encapsulation layer 170. The color filter layer 180 may include color filter patterns 181, 183, and 185 formed corresponding to the pixel regions SP and a second partition wall PW2 formed between the color filter patterns 181, 183, and 185. The color filter patterns 181, 183, and 185 may be disposed corresponding to the light emitting diodes D. Consequently, when white light is output from the light emitting diodes D, the white light may be converted into specific colored light through the color filter patterns 181, 183, and 185. Edges of the color filter patterns 181, 183, and 185 may be curved. When lights of different wavelength bands are output from the light emitting diodes D, the color filter patterns 181, 183, and 185 may be disposed corresponding to the light emitting diodes D. Therefore, the lights of different wavelength bands are substantially prevented from being mixed and causing a blurring phenomenon and/or a ghost phenomenon.

[0059] The color filter patterns 181, 183, and 185 may have a third refractive index and the second partition wall PW2 may have a fourth refractive index lower than the third refractive index. The third refractive index may be in a range of about 1.6 to 1.85 and the fourth refractive index may be in a range of about 1.0 to 1.55, but example embodiments are not limited thereto.

[0060] A middle portion of the second partition wall PW2 may have a bar shape and an upper portion of the second partition wall PW2 may have a shape in which a width progressively increases upward. A width d2 of the middle portion of the second partition wall PW2 may be in a range of 2 μm to 3 μm . The width of the upper portion of the second partition wall PW2 may be larger than or equal to the width d2. However, example embodiments are not limited thereto. A height H2 of the second partition wall PW2 may be in a range of 7 μm to 9 μm , but example embodiments are not limited thereto. The height H2 may be modified in various ways according to a thickness or the like of the color filter patterns 181, 183, and 185. The second partition wall PW2 may be formed of silicon oxide, but example embodiments are not limited thereto. The second partition wall PW2 may also be formed of an air gap.

[0061] Because the second partition wall PW2 may have a refractive index lower than that of the color filter patterns 181, 183, and 185, light that may be incident obliquely on the color filter patterns 181, 183, and 185 from the light-emitting layer 142 of the light emitting diodes D may be reflected by the second partition wall PW2 and may be output to upper areas of the corresponding pixel regions SP. Accordingly, color mixture in a viewing angle direction may be substantially prevented. Additionally, because the second partition wall PW2 between the color filter patterns 181, 183, and 185 has a relatively fine width d2, an emissive area may be increased in comparison to the related art case in which a black matrix may be disposed.

[0062] A scattering layer SL may be disposed on an upper surface of each of the color filter patterns 181, 183, and 185. The scattering layer SL may have a concavo-convex pattern formed on the upper surface of each of the color filter patterns 181, 183, and 185, but example embodiments are not limited thereto. The scattering layer SL may also be

formed of a material layer including beads. Accordingly, light that passes through the color filter patterns **181**, **183**, and **185** and output to the outside may be scattered in various directions.

[0063] A portion of light **L3** may be scattered, and may be incident vertically on the color filter patterns **181**, **183**, and **185** at a boundary between the pixel regions **SP** and toward the second partition wall **PW2**. Therefore, perception of lattices that may occur due to the fine second partition wall **PW2** being viewed as a black area may be substantially prevented when one views an image in a state in which one's eyes are close to a screen, such as when one views an image using a virtual reality (VR) device.

[0064] The second partition wall **PW2** of the electroluminescent display device **100** may be formed corresponding to the first partition wall **PW1**. The first partition wall **PW1** and the second partition wall **PW2** may parallel or substantially parallel to each other in a first direction **1A** perpendicular to the substrate **110**. Because the first partition wall **PW1** and the second partition wall **PW2** may be parallel or substantially parallel to each other in the first direction **1A**, light that may be output from the light emitting diodes **D** respectively formed in the pixel regions **SP** may be output to upper areas of the corresponding pixel regions **SP**. Accordingly, light extraction efficiency may be improved and color mixture may be substantially prevented.

Second Example Embodiment

[0065] In a second example embodiment, descriptions of configurations identical or similar to those of the first example embodiment may be omitted.

[0066] FIG. 4 is a cross-sectional view illustrating an electroluminescent display device according to the second example embodiment of the present disclosure.

[0067] As illustrated in FIG. 4, an electroluminescent display device **200** according to an example embodiment of the present disclosure may include a substrate **210**, thin film transistors **Td1**, **Td2**, and **Td3** and light emitting diodes **D1**, **D2**, and **D3** respectively formed in pixel regions **SP1**, **SP2**, and **SP3** disposed on the substrate **210**. The electroluminescent display device **200** may further include an encapsulation layer **270** disposed on the light emitting diodes **D1**, **D2**, and **D3** and a color filter layer **280** disposed on the encapsulation layer **270**.

[0068] The thin film transistors **Td1**, **Td2**, and **Td3** and the light emitting diodes **D1**, **D2**, and **D3** may be respectively formed in the pixel regions **SP1**, **SP2**, and **SP3** on the substrate **210**. The substrate **210** may also be referred to as a lower substrate, a thin film transistor (TFT) substrate, or a backplane. The pixel regions **SP1**, **SP2**, and **SP3** may include a blue pixel region **SP1**, a red pixel region **SP2**, and a green pixel region **SP3**. However, the pixel regions **SP1**, **SP2**, and **SP3** are not limited thereto and may further include a white pixel region.

[0069] A semiconductor layer **222** may be formed in each of the pixel regions **SP1**, **SP2**, and **SP3**. A gate insulating layer **224** may be formed on the semiconductor layer **222** over the substrate **110** including the pixel regions **SP1**, **SP2**, and **SP3**. A gate electrode **226** may be formed on the gate insulating layer **224** corresponding to the semiconductor layer **222** and an interlayer insulating layer **228** may be formed on the gate electrode **226**. The interlayer insulating layer **228** and the gate insulating layer **224** may include first

and second contact holes **CH1** and **CH2** configured to respectively expose the source area and the drain area of the semiconductor layer **222**.

[0070] A source electrode **232** and a drain electrode **230** spaced apart from each other may be formed on the interlayer insulating layer **228** corresponding to the semiconductor layer **222**. The source electrode **232** and the drain electrode **230** may be respectively connected to the source area and the drain area of the semiconductor layer **222** through the first and second contact holes **CH1** and **CH2**. The semiconductor layer **222**, the gate electrode **226**, the source electrode **232**, and the drain electrode **230** formed in the pixel regions **SP1**, **SP2**, and **SP3** may constitute the thin film transistors **Td1**, **Td2**, and **Td3**.

[0071] A passivation layer **234** may be formed on each of the thin film transistors **Td1**, **Td2**, and **Td3**. The passivation layer **234** may include a third contact hole **CH3** configured to expose the source electrode **232**. In the electroluminescent display device **200**, holes **h1** and **h2** configured to partition the pixel regions **SP1**, **SP2**, and **SP3** may be formed in the interlayer insulating layer **228** and the passivation layer **234**. The light emitting diodes **D1**, **D2**, and **D3** may be partitioned by the holes **h1** and **h2** in the interlayer insulating layer **228** and the passivation layer **234** so that the light emitting diodes **D1**, **D2**, and **D3** respectively correspond to the pixel regions **SP1**, **SP2**, and **SP3**.

[0072] The light emitting diodes **D1**, **D2**, and **D3** may be spaced apart from each other and may be respectively disposed in the pixel regions **SP1**, **SP2**, and **SP3**. In the electroluminescent display device **200**, a width of a portion of the hole **h1** formed in the interlayer insulating layer **228** may be larger than a width of a portion of the hole **h1** formed in the passivation layer **234**. The electroluminescent display device **200** may have an under-cut form in which the width of the interlayer insulating layer **228** may be smaller than the width of the passivation layer **234** disposed in each of the pixel regions **SP1**, **SP2**, and **SP3**.

[0073] A first electrode **241** may be configured to cover an upper surface and a side surface of the passivation layer **234**. The first electrode **241** may be connected to the source electrode **232** of each of the thin film transistors **Td1**, **Td2**, and **Td3** through the third contact hole **CH3** formed in the passivation layer **234** and may be separately formed in each of the pixel regions **SP1**, **SP2**, and **SP3**.

[0074] Because the interlayer insulating layer **228** and the passivation layer **234** of the electroluminescent display device **200** may have an under-cut form, the first electrode **241** separately formed in each of the pixel regions **SP1**, **SP2**, and **SP3** may be formed by a single process. Therefore, a process of forming the electroluminescent display device according to example embodiments of the present disclosure may be simplified.

[0075] An insulating pattern **IP** may be configured to cover a side surface and a portion of an upper surface of the first electrode **241**. The insulating pattern **IP** may be formed of silicon oxide, but example embodiments are not limited thereto. The insulating pattern **IP** may mitigate a step difference of the first electrode **241** and may improve current efficiency. For example, when forming a light-emitting layer **242** on the first electrode **241**, the light-emitting layer **242** may be formed to have a relatively small thickness on a stepped area of the first electrode **241**. Therefore, a current that does not contribute to emission may be substantially prevented from being focused.

[0076] The light-emitting layer 242 may be configured to cover the first electrode 241 and the insulating pattern IP. Because the interlayer insulating layer 228 and the passivation layer 234 of the electroluminescent display device 200 may have the under-cut form, the light-emitting layer 242 separately formed in each of the pixel regions SP1, SP2, and SP3 may be formed by a single process. The light-emitting layer 242 may emit white light, but example embodiments are not limited thereto. A light-emitting layer 242 configured to emit one of blue light, red light, and green light may be disposed in each of the pixel regions SP1, SP2, and SP3. A luminescent material of the light-emitting layer 242 may be made of one or more organic luminescent materials having a refractive index of about 1.8 or higher or one or more inorganic luminescent materials, such as a quantum dot.

[0077] A second electrode 243 may be configured to cover an upper surface and a side surface of the light-emitting layer 242. In some embodiments, as illustrated in FIG. 4, the second electrode 243 may be formed separately in each of the pixel regions SP1, SP2, and SP3. In other embodiments, the second electrodes 243 may be connected to each other in a cross-sectional view taken along a direction perpendicular to that of the cross-sectional view illustrated in FIG. 4. Accordingly, the first electrode 241, the insulating pattern IP, the light-emitting layer 242, and the second electrode 243 may form each of the light emitting diodes D1, D2, and D3. The light emitting diodes D1, D2, and D3 may be spaced apart from each other and may be disposed corresponding to the pixel regions SP1, SP2, and SP3, respectively.

[0078] The encapsulation layer 270 may be disposed on the light emitting diodes D1, D2, and D3 formed corresponding to the pixel regions SP1, SP2, and SP3, respectively. The encapsulation layer 270 of the electroluminescent display device 200 may include an encapsulation film 271 having a first refractive index and a first partition wall PW1 having a second refractive index lower than the first refractive index. The encapsulation film 271 may cover each of the light emitting diodes D1, D2, and D3 formed corresponding to each of the pixel regions SP1, SP2, and SP3. The encapsulation film 271 may be formed of an inorganic film and/or have a multilayer structure.

[0079] A residual layer OM may be present between the light emitting diodes D1, D2, and D3. The residual layer OM may be formed from one or more materials remaining in the hole h1 of the interlayer insulating layer 228 that may be used in forming the light emitting diodes D1, D2, and D3 and the encapsulation film 271.

[0080] The first partition wall PW1 may be disposed between the encapsulation films 271 corresponding to the boundary between the pixel regions SP1, SP2, and SP3. Although a middle portion of the first partition wall PW1 may be illustrated in FIG. 4 as having a bar shape and an upper portion of the first partition wall PW1 may be illustrated as having a shape in which a width progressively increases in the drawings, these are merely examples. The first partition wall PW1 may be formed such that the upper portion and the middle portion have the same or substantially the same width. A lower portion of the first partition wall PW1 of the electroluminescent display device 200 may be formed to have a width larger than that of the middle portion. A lower surface of the first partition wall PW1 may contact the residual layer OM.

[0081] The first partition wall PW1 may be made of one or more organic materials having a second refractive index

lower than the first refractive index of the encapsulation film 271. For example, the first refractive index may be in a range of about 1.6 to 1.85 and the second refractive index may be in a range of about 1.0 to 1.55, but example embodiments are not limited thereto. Because the first partition wall PW1 may have a refractive index lower than that of the encapsulation film 271, light that may be incident obliquely on the encapsulation film 271 from the light-emitting layer 242 of the light emitting diodes D1, D2, and D3 may be reflected by the first partition wall PW1 and may be output to upper areas of the corresponding pixel regions SP1, SP2, and SP3. Accordingly, light extraction efficiency of the electroluminescent display device 200 may be improved and color mixture may be substantially prevented. In addition, permeation of oxygen and/or moisture into the light-emitting layer 242 and the second electrode 243 may be more substantially prevented by the encapsulation films 271 and the first partition wall PW1 disposed between the encapsulation films 271 configured to cover the light emitting diodes D1, D2, and D3. Because the width of the lower portion of the first partition wall PW1 may be larger than the width of the middle portion thereof and the lower surface of the first partition wall PW1 may have a structure in which the lower surface contacts the residual layer OM, efficiency may be improved. For example, substantial prevention of permeation of oxygen and/or moisture may be achieved.

[0082] The color filter layer 280 may be disposed on the encapsulation layer 270. The color filter layer 280 may include color filter patterns 281, 283, and 285 formed corresponding to the pixel regions SP1, SP2, and SP3, respectively, and second partition walls PW2 formed between the color filter patterns 281, 283, and 285. Edges of the color filter patterns 281, 283, and 285 may be curved. The color filter patterns 281, 283, and 285 may have a third refractive index and the second partition wall PW2 may have a fourth refractive index lower than the third refractive index. The third refractive index may be in a range of about 1.6 to 1.85 and the fourth refractive index may be in a range of about 1.0 to 1.55, but example embodiments are not limited thereto. The second partition wall PW2 may be formed of silicon oxide, but example embodiments are not limited thereto.

[0083] Because the second partition wall PW2 may have a refractive index lower than that of the color filter patterns 281, 283, and 285, light that may be incident obliquely on the color filter patterns 281, 283, and 285 from the light-emitting layer 242 of the light emitting diodes D1, D2, and D3 may be reflected by the second partition wall PW2 and may be output to upper areas of the corresponding pixel regions SP1, SP2, and SP3. Accordingly, color mixture in a viewing angle direction may be substantially prevented. Because the second partition wall PW2 between the color filter patterns 281, 283, and 285 may have a relatively fine width, an emissive area may be increased in comparison to a related art case in which a black matrix may be disposed.

[0084] The second partition wall PW2 of the electroluminescent display device 200 may be formed corresponding to the first partition wall PW1. For example, the first partition wall PW1 and the second partition wall PW2 may be parallel or substantially parallel to each other in a first direction perpendicular to the substrate 210. Because the first partition wall PW1 and the second partition wall PW2 may be parallel or substantially parallel to each other in the first direction, light that may be output from the light emitting diodes D1,

D2, and D3 respectively formed in the pixel regions SP1, SP2, and SP3 may be output to upper areas of the corresponding pixel regions SP1, SP2, and SP3. Accordingly, light extraction efficiency may be improved and color mixture may be substantially prevented.

[0085] FIG. 5 is an enlarged view of a portion of an electroluminescent display device according to the second example embodiment of the present disclosure.

[0086] Although not illustrated in FIG. 5, the electroluminescent display device 200 of FIG. 4 may include the substrate 210 of FIG. 4. Light emitting diodes D may be disposed on the substrate 210 of FIG. 4, an encapsulation layer 270 may be disposed on the light emitting diodes D, and a color filter layer 280 may be disposed on the encapsulation layer 270. An interlayer insulating layer 228 and a passivation layer 234 may be disposed between the substrate 210 and the light emitting diodes D. Because holes h1 and h2 configured to partition pixel regions SP may be formed in the interlayer insulating layer 228 and the passivation layer 234, the light emitting diodes D may be spaced apart from each other and disposed in the pixel regions SP, respectively.

[0087] Because holes h1 and h2 may be formed in the passivation layer 234 and the interlayer insulating layer 228, a bank layer that may be formed in a related art electroluminescent display device to partition pixel regions SP may be omitted. Therefore, a process of forming the electroluminescent display device according to example embodiments of the present disclosure may be simplified.

[0088] The electroluminescent display device 200 may have an under-cut form in which the width of the interlayer insulating layer 228 may be smaller than the width of the passivation layer 234 disposed in each of the pixel regions SP. A first electrode 241 may be configured to cover an upper surface and a side surface of the passivation layer 234. Because the interlayer insulating layer 228 and the passivation layer 234 may have the under-cut form, the first electrode 241 separately formed in each of the pixel regions SP may be formed by a single process. Therefore, a process of forming the electroluminescent display device according to example embodiments of the present disclosure may be simplified.

[0089] An insulating pattern IP may be configured to cover a side surface and a portion of an upper surface of the first electrode 241. When forming a light-emitting layer 242 on the first electrode 241 using such an insulating pattern IP, the light-emitting layer 242 may be formed to have a relatively small thickness on a stepped area of the first electrode 241. Therefore, a current that does not contribute to emission may be substantially prevented from being focused, thus improving current efficiency. The light-emitting layer 242 may be configured to cover the first electrode 241 and the insulating pattern IP. Because the interlayer insulating layer 228 and the passivation layer 234 of the electroluminescent display device 200 may have the under-cut form, the light-emitting layer 242 separately formed in each of the pixel regions SP may be formed by a single process. The second electrode 243 may be configured to cover an upper surface and a side surface of the light-emitting layer 242. The first electrode 241, the insulating pattern IP, the light-emitting layer 242, and the second electrode 243 may form each of the light emitting diodes D and the light emitting diodes D may be separated from each other and disposed corresponding to the pixel regions SP, respectively.

[0090] The encapsulation layer 270 may be disposed on the light emitting diodes D formed corresponding to the pixel regions SP, respectively. The encapsulation layer 270 may include an encapsulation film 271 having a first refractive index and a first partition wall PW1 having a second refractive index lower than the first refractive index. The encapsulation film 271 may cover each of the light emitting diodes D formed corresponding to each of the pixel regions SP. The encapsulation film 271 may be formed of an inorganic film and/or have a multilayer structure. Because the encapsulation film 271 may cover each of the light emitting diodes D, permeation of oxygen and/or moisture into the light-emitting layer 242 and/or the second electrode 243 may be substantially prevented.

[0091] A residual layer OM may be present between the light emitting diodes D. The residual layer OM may be formed from one or more materials that may be used in forming the light emitting diodes D and the encapsulation film 271 remaining in the hole h1 of the interlayer insulating layer 228.

[0092] The first partition wall PW1 may be disposed between the encapsulation films 271 corresponding to the boundary between the pixel regions SP. Although a middle portion of the first partition wall PW1 may be illustrated in FIG. 5 as having a bar shape and an upper portion of the first partition wall PW1 may be illustrated as having a shape in which a width progressively increases, this is merely an example. The first partition wall PW1 may be formed such that the upper portion and the middle portion have the same or substantially the same width. A lower portion of the first partition wall PW1 of the electroluminescent display device 200 may be formed to have a width larger than that of the middle portion and a lower surface of the first partition wall PW1 may contact the residual layer OM. A width d1 of the middle portion of the first partition wall PW1 may be in a range of about 2 μm to 3 μm . The width of the upper portion of the first partition wall PW1 may be greater than or equal to the width d1 of the middle portion of the first partition wall PW1. However, example embodiments are not limited thereto and the size and form of the first partition wall PW1 may be modified in various ways according to, for example, the size and/or resolution of the pixel regions SP. A height H1 of the first partition wall PW1 may be in a range of about 7 μm to 9 μm , but example embodiments are not limited thereto. The height H1 may be modified in various ways according to, for example, a thickness of the passivation layer 234, the interlayer insulating layer 228, and/or the light emitting diodes D.

[0093] The first partition wall PW1 may be made of one or more organic materials having a second refractive index lower than the first refractive index of the encapsulation film 271. For example, the first refractive index may be in a range of about 1.6 to 1.85 and the second refractive index may be in a range of about 1.0 to 1.55, but example embodiments are not limited thereto. Because the first partition wall PW1 may have a refractive index lower than that of the encapsulation film 271, light that may be incident obliquely on the encapsulation film 271 from the light-emitting layer 242 of the light emitting diodes D may be reflected by the first partition wall PW1 and may be output upward. Accordingly, light extraction efficiency of the electroluminescent display device 200 may be improved and color mixture may be substantially prevented. Additionally, by forming the first partition wall PW1 between the encapsulation films 271

configured to respectively cover the light emitting diodes D, efficiency of substantially preventing infiltration of oxygen and/or moisture into the light-emitting layer 242 and/or the second electrode 243 may be improved. Finally, because the width of the lower portion of the first partition wall PW1 may be greater than the width of the middle portion thereof and the lower surface of the first partition wall PW1 may have a structure in which the lower surface contacts the residual layer OM, stability of the light emitting diodes D may be further improved.

[0094] The color filter layer 280 may be disposed on the encapsulation layer 270. The color filter layer 280 may include color filter patterns 281, 283, and 285 formed corresponding to the pixel regions SP, respectively, and a second partition wall PW2 formed between the color filter patterns 281, 283, and 285. The color filter patterns 281, 283, and 285 may have a third refractive index and the second partition wall PW2 may have a fourth refractive index lower than the third refractive index. The third refractive index may be in a range of about 1.6 to 1.85 and the fourth refractive index may be in a range of about 1.0 to 1.55, but example embodiments are not limited thereto.

[0095] A width d2 of a middle portion of the second partition wall PW2 may be in a range of 2 μm to 3 μm . A width of an upper portion of the second partition wall PW2 may be larger than or equal to the width d2 of the middle portion of the second partition wall PW2. However, example embodiments are not limited thereto. A height H2 of the second partition wall PW2 may be in a range of about 7 μm to 9 μm , but example embodiments are not limited thereto. The height H2 may be modified in various ways according to, for example, a thickness of the color filter patterns 281, 283, and 285. The second partition wall PW2 may be formed of silicon oxide, but example embodiments are not limited thereto. The second partition wall PW2 may also be formed of an air gap.

[0096] Because the second partition wall PW2 may have a refractive index lower than that of the color filter patterns 281, 283, and 285, light L2 that may be incident obliquely on the color filter patterns 281, 283, and 285 from the light-emitting layer 242 of the light emitting diodes D may be reflected by the second partition wall PW2 and may be output upward. Accordingly, color mixture occurs in a viewing angle direction may be substantially prevented. Because the second partition wall PW2 between the color filter patterns 281, 283, and 285 may have a relatively fine width d2, an emissive area may be increased in comparison to the related art case in which a black matrix may be disposed.

[0097] A scattering layer SL may be disposed on an upper surface of each of the color filter patterns 281, 283, and 285. The scattering layer SL may have a concavo-convex pattern formed on the upper surface of each of the color filter patterns 281, 283, and 285, but example embodiments are not limited thereto. The scattering layer SL may also be formed of one or more material layers including beads. Accordingly, light that passes through the color filter patterns 281, 283, and 285 and output to the outside may be scattered in various directions. By scattering a portion of light L3 that may be incident vertically on the color filter patterns 281, 283, and 285 at a boundary between the pixel regions SP toward the second partition wall PW2, perception of lattices may occur due to the fine second partition wall PW2 being viewed as a black area. Such perception of

lattices may be substantially prevented when one views an image in a state in which one's eyes are close to a screen, such as when one views an image using a VR device.

[0098] The second partition wall PW2 of the electroluminescent display device 200 of FIG. 5 may be formed corresponding to the first partition wall PW1. The first partition wall PW1 and the second partition wall PW2 may be parallel to each other in a first direction 1A perpendicular to the substrate 110 of FIG. 4. Because the first partition wall PW1 and the second partition wall PW2 may be parallel to each other in the first direction 1A, light that may be output from the light emitting diodes D respectively formed in the pixel regions SP may be output to upper areas of the corresponding pixel regions SP. Accordingly, light extraction efficiency may be improved and color mixture may be substantially prevented.

[0099] FIG. 6 is a graph illustrating light extraction efficiency according to refractive indices of first and second partition walls according to the first and second example embodiments of the present disclosure.

[0100] As illustrated in FIG. 6, light extraction efficiency may change according to changes in refractive indices of first and second partition walls PW1 and PW2 of FIG. 5 when refractive indices of an encapsulation film 271 of FIG. 5 and color filter patterns 281, 283, and 285 of FIG. 5 are about 1.7. Light extraction efficiency may increase as the refractive indices of the first and/or second partition walls PW1 and PW2 of FIG. 5 decrease from about 1.55 to about 1.4.

[0101] Light extraction efficiency may be about 47% when the refractive indices of the first and/or second partition walls PW1 and PW2 of FIG. 5 are about 1.55. Light extraction efficiency may be about 51% when the refractive indices of the first and/or second partition walls PW1 and PW2 of FIG. 5 are about 1.5. Light extraction efficiency may be about 55.5% when the refractive indices of the first and/or second partition walls PW1 and PW2 of FIG. 5 are about 1.45. Light extraction efficiency may be about 59% when the refractive indices of the first and/or second partition walls PW1 and PW2 of FIG. 5 are about 1.4. Accordingly, light extraction efficiency may be greatest when the refractive indices of the first and/or second partition walls PW1 and PW2 of FIG. 5 are about 1.4. For example, a path of light that may be obliquely output outward from light emitting diodes D may be adjusted through the first and/or second partition walls PW1 and PW2 of FIG. 5. The largest amount of light may be output to the outside when the refractive indices of the first and second partition walls PW1 and PW2 of FIG. 5 are about 1.4. Accordingly, light extraction efficiency may be improved by setting the refractive indices of the first and/or second partition walls PW1 and PW2 of FIG. 5 of the electroluminescent display device 100 of FIG. 2 and the electroluminescent display device 200 of FIG. 4 according to embodiments of the present disclosure to be about 1.4.

[0102] In the present disclosure, a first partition wall having a low refractive index may be disposed between light emitting diodes. Accordingly, a path of light that may not be output to the outside because it may be totally reflected inside the light emitting diodes may be changed and the light may be allowed to be output to the outside. Accordingly, light extraction efficiency may be improved. A second partition wall having a low refractive index may be disposed between color filter patterns. Accordingly, a path of light that may travel to an adjacent pixel region may be changed and

the light may be allowed to be output to a corresponding pixel region, thus substantially preventing color mixture.

[0103] It will be apparent to those skilled in the art that various modifications and variations may be made in the electroluminescent display device of the present disclosure without departing from the technical idea or scope of the disclosure. Thus, it is intended that the present disclosure cover the modifications and variations of this disclosure, provided that they come within the scope of the appended claims and their equivalents.

What is claimed is:

1. An electroluminescent display device comprising:
 - a substrate including a plurality of pixel regions;
 - a plurality of light emitting diodes spaced apart from each other on the substrate and each corresponding to the plurality of pixel regions, respectively;
 - a plurality of encapsulation films respectively covering each of the light emitting diodes of the plurality of light emitting diodes, wherein the plurality of encapsulation films has a first refractive index;
 - a first partition wall disposed between each of the encapsulation films of the plurality of encapsulation films, wherein the first partition wall corresponds to a boundary between the plurality of pixel regions and has a second refractive index lower than the first refractive index; and
 - a color filter layer disposed on the plurality of encapsulation films and the first partition wall,
 - wherein the color filter layer includes a plurality of color filter patterns having a third refractive index and the color filter layer further includes a second partition wall disposed between each of the plurality of color filter patterns, and
 - wherein the second partition wall has a fourth refractive index lower than the third refractive index.
2. The electroluminescent display device of claim 1, wherein the second partition wall is disposed corresponding to the first partition wall.
3. The electroluminescent display device of claim 2, wherein the second partition wall is parallel to the first partition wall in a direction perpendicular to the substrate.
4. The electroluminescent display device of claim 1, wherein each of the plurality of color filter patterns is disposed to correspond to each of the plurality of light emitting diodes, respectively.
5. The electroluminescent display device of claim 1, wherein a middle portion of each of the first partition wall and the second partition wall has a bar shape and an upper

portion of each of the first partition wall and the second partition wall has a width that progressively increases in an upward direction.

6. The electroluminescent display device of claim 5, wherein a width of the middle portion of each of the first partition wall and the second partition wall is in a range of 2 micrometers to 3 micrometers, inclusive.

7. The electroluminescent display device of claim 5, wherein a height of each of the first partition wall and the second partition wall is in a range of 7 micrometers to 9 micrometers, inclusive.

8. The electroluminescent display device of claim 1, wherein each of the second refractive index and the fourth refractive index is in a range of 1.0 to 1.55, inclusive.

9. The electroluminescent display device of claim 1, wherein the color filter layer further includes a scattering layer disposed on an upper surface of each of the plurality of color filter patterns.

10. The electroluminescent display device of claim 9, wherein the scattering layer has a concavo-convex pattern.

11. The electroluminescent display device of claim 9, wherein the scattering layer is formed of one or more materials including beads.

12. The electroluminescent display device of claim 1, wherein an edge of each of the plurality of color filter patterns is curved.

13. The electroluminescent display device of claim 1, wherein each of the plurality of light emitting diodes includes:

- a first electrode disposed on a passivation layer;
- an insulating pattern configured to cover an edge of the first electrode;
- a light-emitting layer disposed on the first electrode and the insulating pattern; and
- a second electrode disposed on the light-emitting layer.

14. The electroluminescent display device of claim 13, further including an interlayer insulating layer disposed under the passivation layer, wherein the passivation layer and the interlayer insulating layer are separated in each pixel region by the first partition wall.

15. The electroluminescent display device of claim 13, wherein a width of a first portion of the light-emitting layer on the first electrode is greater than a width of a second portion of the light-emitting layer on the insulating pattern.

* * * * *

专利名称(译)	电致发光显示装置		
公开(公告)号	US20190172874A1	公开(公告)日	2019-06-06
申请号	US16/210375	申请日	2018-12-05
[标]申请(专利权)人(译)	乐金显示有限公司		
申请(专利权)人(译)	LG DISPLAY CO. , LTD.		
当前申请(专利权)人(译)	LG DISPLAY CO. , LTD.		
[标]发明人	PARK HAN SUN BANG HYUNG SEOK PARK JI YEON		
发明人	LIM, HYEONG-JUN PARK, HAN-SUN BANG, HYUNG-SEOK PARK, JI-YEON		
IPC分类号	H01L27/32 H01L51/52 H01L51/50		
CPC分类号	H01L27/322 H01L51/5256 H01L51/5206 H01L51/5221 H01L51/5012 H01L27/3211 H01L27/3244 H01L51/5268 H01L51/5271 H01L51/5275		
优先权	1020170166006 2017-12-05 KR		
其他公开文献	US10700140		
外部链接	Espacenet USPTO		

摘要(译)

公开了一种电致发光显示装置。所公开的电致发光显示装置包括包括多个像素区域的基板;多个发光二极管分别在基板上彼此隔开,并且每个发光二极管分别对应于多个像素区域;多个封装膜,分别覆盖多个发光二极管中的每个发光二极管,其中,所述多个封装膜具有第一折射率;第一分隔壁,设置在所述多个封装膜的每个封装膜之间,其中,所述第一分隔壁对应于所述多个像素区域之间的边界,并且具有低于所述第一折射率的第二折射率;滤色器层设置在多个封装膜和第一分隔壁上。

